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(54) **Title:** GAS INTAKE ASSEMBLY, SEMICONDUCTOR PROCESS CHAMBER AND SEMICONDUCTOR PROCESS METHOD

(54) 发明名称: 进气组件、半导体工艺腔室及半导体工艺方法

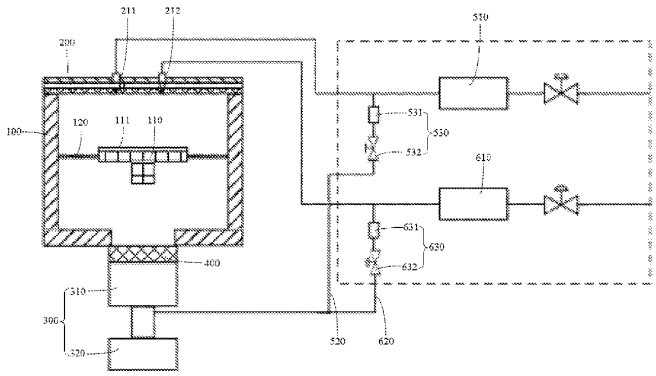


图 1

(57) **Abstract:** The present application relates to the technical field of semiconductors. Disclosed are a gas intake assembly, a semiconductor process chamber and a semiconductor process method. The gas intake assembly comprises a gas intake window and a switching valve plate which are connected to each other, wherein the gas intake window is provided with a first gas inlet and a second gas inlet; the switching valve plate can move between a first position and a second position relative to the gas intake window, and the switching valve plate is provided with a gas path in communication with a gas output end of the gas intake assembly; and when the switching valve plate is located in the first position, the first gas inlet is in communication with the gas path, and the second gas inlet is not in communication with the gas path; and when the switching valve plate is located in the second position, the second gas inlet is in communication with the gas path, and the first gas inlet is not in communication with the gas path. In this way, by means of adjusting the position of the switching valve plate, gas from a previous process can be directly cut off at the position of the gas intake window, in order to prevent residual gas from the previous process from participating in the next process, thereby facilitating an improvement in a process effect.

WO 2025/185503 A1

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本国际公布:
— 包括国际检索报告(条约第21条(3))。

(57) 摘要: 本申请公开一种进气组件、半导体工艺腔室及半导体工艺方法，属于半导体技术领域。进气组件包括相连的进气窗和切换阀板，进气窗设有第一气体进气口和第二气体进气口，切换阀板可相对于进气窗在第一位置和第二位置之间运动，且切换阀板设有气路，气路与进气组件的出气端连通；在切换阀板位于第一位置的情况下，第一气体进气口与气路连通且第二气体进气口与气路断开；在切换阀板位于第二位置的情况下，第二气体进气口与气路连通且第一气体进气口与气路断开。如此，通过调节切换阀板的位置，可直接在进气窗的位置截断上一工艺的气体，避免上一工艺的残留气体参与下一工艺过程，有利于提升工艺效果。